
RX600 & RX200 Series

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Reprogramming the On-Chip Flash Memory Using Simple Flash API for RX

Abstract

The latest Simple Flash API includes definitions associated with the Firmware Integration Technology (FIT). When using the Simple Flash API with a non-FIT project, many of those definitions are not necessary.

This application note describes the method to implement the Simple Flash API without unnecessary definitions for a non-FIT project.

Products

- RX610 Group
- RX62N, RX621, RX62T, and RX62G Groups
- RX630, RX63N, RX631, and RX63T Groups
- RX210, RX21A, and RX220 Groups

When using this application note with other Renesas MCUs, careful evaluation is recommended after making modifications to comply with the alternate MCU.

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1. Specifications

In this application note, the Simple Flash API is modified to have only necessary definitions for a non-FIT project to implement the definitions in the user non-FIT project. The RX210 Group Initial Setting application note is used as an example of a non-FIT project here.

Figure 1.1 shows the Implementing the API.

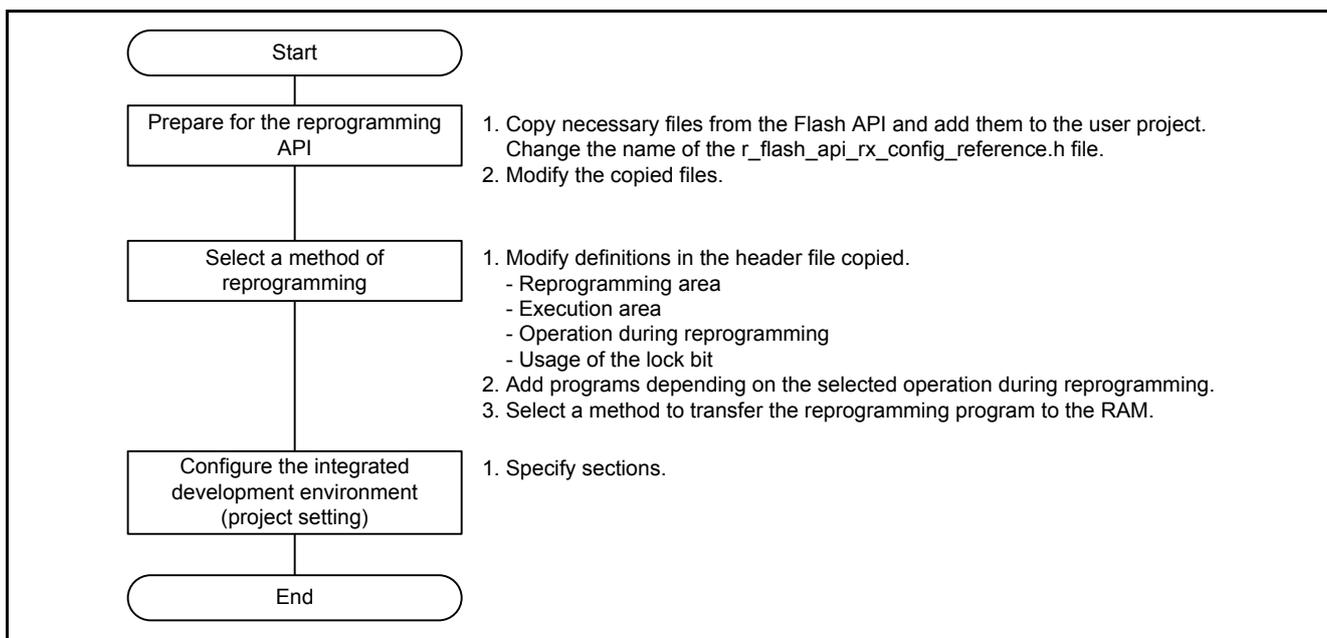


Figure 1.1 Implementing the API

The sample code accompanying this application note includes the sample code from the RX210 Group Initial Setting as well as the sample code for the reprogramming program (`flash_api` function).

With the sample code for the reprogramming program, when reprogramming of the E2 DataFlash (flash memory for storing data) is enabled, erasing, programming, and verification of the E2 DataFlash are executed. Subsequently, when reprogramming of the ROM (flash memory for storing code) is enabled, erasing, programming, and verification of the ROM are executed.

2. Operation Confirmation Conditions

The sample code accompanying this application note has been run and confirmed under the conditions below.

Table 2.1 Operation Confirmation Conditions

Item	Contents
MCU used	R5F5210BBDFP (RX210 Group)
Operating frequencies	- Main clock: 20 MHz - PLL: 100 MHz (main clock divided by 2 and multiplied by 10) - System clock (ICLK): 50 MHz (PLL divided by 2) - Peripheral module clock B (PCLKB): 25 MHz (PLL divided by 4) - FlashIF clock (FCLK): 25 MHz (PLL divided by 4)
Operating voltage	5.0 V
Integrated development environment	Renesas Electronics Corporation High-performance Embedded Workshop Version 4.09.01
C compiler	Renesas Electronics Corporation C/C++ Compiler Package for RX Family V.1.02 Release 01 Compile options -cpu=rx200 -output=obj="\$ (CONFIGDIR)\\$(FILELEAF).obj" -debug -nologo (The default setting is used in the integrated development environment.)
iodefine.h version	Version 1.4
Endian	Little endian
Operating mode	Single-chip mode
Processor mode	Supervisor mode
Sample code version	Version 1.00
Board used	Renesas Starter Kit for RX210 (product part no.: R0K505210C002BE)

3. Reference Application Notes

For additional information associated with this document, refer to the following application notes.

- RX210 Group Initial Setting Rev. 2.20 (R01AN1002EJ) ⁽¹⁾
- RX600 & RX200 Series Simple Flash API for RX Rev.2.50 (R01AN0544EU)

Note:

1. The initial setting functions in the RX210 Group Initial Setting application note above are used in the sample code in this application note. The revision number of the RX210 Group Initial Setting application note is current as of when this application note was made. However the latest version is always recommended. Visit the Renesas Electronics Corporation website to check and download the latest version.

4. Preparing for the Reprogramming Program

4.1 Adding Necessary Files from the Flash API

Copy the following files from the Simple Flash API project to add them to the user project.

The locations in the brackets below indicate original locations in the Simple Flash API project.

- r_flash_api_rx_if.h (location: \r_flash_api_rx)
- r_flash_api_rx210.h (location: \r_flash_api_rx\src\targets\rx210)
- r_flash_api_rx.c (location: \r_flash_api_rx\src)
- r_flash_api_rx_config_reference.h (location: \r_flash_api_rx\ref)

Rename the r_flash_api_rx_config_reference.h file to r_flash_api_rx_config.h when adding to the user project.

4.2 Modifying r_flash_api_rx_if.h

The r_flash_api_rx_if.h file needs to be modified as follows:

- Delete platform.h.

```
// /* Used to get which MCU is currently being used. */
// #include "platform.h"
```

- Delete read processing in r_flash_api_rxXXX.h.

```
/* Memory specifics for the each MCU group */
// #if defined(BSP_MCU_RX610)
//     #include "./src/targets/rx610/r_flash_api_rx610.h"
// #elif defined(BSP_MCU_RX621) || defined(BSP_MCU_RX62N)
//     #include "./src/targets/rx62n/r_flash_api_rx62n.h"
// #elif defined(BSP_MCU_RX62T)
//     #include "./src/targets/rx62t/r_flash_api_rx62t.h"
// #elif defined(BSP_MCU_RX62G)
//     #include "./src/targets/rx62g/r_flash_api_rx62g.h"
// #elif defined(BSP_MCU_RX630)
//     #include "./src/targets/rx630/r_flash_api_rx630.h"
// #elif defined(BSP_MCU_RX631) || defined(BSP_MCU_RX63N)
//     #include "./src/targets/rx63n/r_flash_api_rx63n.h"
// #elif defined(BSP_MCU_RX63T)
//     #include "./src/targets/rx63t/r_flash_api_rx63t.h"
// #elif defined(BSP_MCU_RX210)
//     #include "./src/targets/rx210/r_flash_api_rx210.h"
// #elif defined(BSP_MCU_RX21A)
//     #include "./src/targets/rx21a/r_flash_api_rx21a.h"
// #elif defined(BSP_MCU_RX220)
//     #include "./src/targets/rx220/r_flash_api_rx220.h"
// #else
//     #error "!!! No 'targets' folder for this MCU Group !!!"
// #endif
```

4.3 Modifying r_flash_api_rx210.h

The r_flash_api_rx210.h file needs to be modified as follows:

- Add definitions.

```
#define BSP_ROM_SIZE_BYTES (524288)
#define BSP_RAM_SIZE_BYTES (65536)
#define BSP_DATA_FLASH_SIZE_BYTES (8192)

#define ROM_PE_ADDR ((0x10000000-BSP_ROM_SIZE_BYTES)&(0x00FFFFFF))

#define BSP_ICLK_HZ (50000000)
#define BSP_FCLK_HZ (25000000)

/* FCU-RAM address define */
/* FCU F/W Store Address */
#define FCU_PRG_TOP (0xFEFFE000)
/* FCU RAM Address */
#define FCU_RAM_TOP (0x007F8000)
/* FCU RAM Size */
#define FCU_RAM_SIZE (0x2000)
```

Note: • Modify the values of these definitions according to the MCU used and the user system.

- Add the hardware lock mcu_lock_t.

```
typedef enum
{
    BSP_LOCK_FLASH = 0,
    BSP_NUM_LOCKS //This entry is not a valid lock. It is used for sizing g_bsp_Locks[] array below.
                  Do not touch!
} mcu_lock_t;
```

4.4 Modifying r_flash_api_rx.c

The r_flash_api_rx.c file needs to be modified as follows:

- Add #include for stdint.h and stdbool.h.

```
#include <stdint.h>
#include <stdbool.h>
```

- Replace #include "mcu_info.h" with "r_flash_api_rx210.h".

```
// #include "mcu_info.h"
#include "r_flash_api_rx210.h"
```

- Delete #include for "platform.h" and "r_flash_api_rx_private.h".

```
// #include "platform.h"
// #include "r_flash_api_rx_private.h"
```

- Modify the directory level of iodef.h according to the user project.
The following shows an example when the directory of iodef.h is one level above the directory of r_flash_api_rx.c.

```
// #include "iodef.h"
#include "../iodef.h"
```

- Add functions R_BSP_HardwareLock and R_BSP_HardwareUnlock

```
bool R_BSP_HardwareLock(mcu_lock_t const hw_index);
bool R_BSP_HardwareUnlock(mcu_lock_t const hw_index);
```

```

/*****
* Function Name: R_BSP_HardwareLock
* Description: Attempt to acquire the lock that has been sent in. This function takes in a peripheral index into
*              the array that holds hardware locks.
* Arguments: hw_index -
*            Index in locks array to the hardware resource to lock.
* Return Value: true -
*              Lock was acquired.
*              false -
*              Lock was not acquired.
*****/
bool R_BSP_HardwareLock (mcu_lock_t const hw_index)
{
    return true;
} /* End of function R_BSP_HardwareLock() */
/*****
* Function Name: R_BSP_HardwareUnlock
* Description: Release hold on lock.
* Arguments: hw_index -
*            Index in locks array to the hardware resource to unlock.
* Return Value: true -
*              Lock was released.
*              false -
*              Lock was not released.
*****/
bool R_BSP_HardwareUnlock (mcu_lock_t const hw_index)
{
    return true;
} /* End of function R_BSP_HardwareUnlock() */

```

5. Selecting a Method of Reprogramming

This section describes methods of reprogramming with selection of a reprogramming area, an execution area, an operation during reprogramming, and a RAM transfer method.

5.1 Specifying a Method of Reprogramming

Operations and control methods vary depending on the selected reprogramming area, execution area, and operation during reprogramming. Select one of the methods listed in Table 5.1 and configure `r_flash_api_rx_config.h` accordingly.

Table 5.2 to Table 5.12 list settings in `r_flash_api_rx_config.h`. Numbers in table titles correspond to numbers in Table 5.1.

Table 5.1 Methods of Reprogramming

No.	Reprogramm- ing Area	Program Execution Area	Operation During Reprogramming	Lock Bit Protection (ROM Only)
1	ROM, E2 DataFlash	RAM	Subsequent processing not executed ⁽¹⁾	Disabled by the API
2			Subsequent processing executed ⁽²⁾	Disabled by the API
3			Subsequent processing not executed ⁽¹⁾	Disabled by the user program
4			ROM: Subsequent processing not executed ⁽¹⁾ E2 DataFlash: Subsequent processing executed ⁽²⁾	Disabled by the user program ⁽³⁾
5	ROM	RAM	Subsequent processing not executed ⁽¹⁾	Disabled by the API
6			Subsequent processing executed ⁽²⁾	Disabled by the API
7			Subsequent processing not executed ⁽¹⁾	Disabled by the user program
8	E2 DataFlash	RAM	Subsequent processing not executed ⁽¹⁾	—
9			Subsequent processing executed ⁽²⁾	
10		ROM	Subsequent processing not executed ⁽¹⁾	
11			Subsequent processing executed ⁽²⁾	

Notes:

1. Waits for completion of reprogramming processing, and the subsequent processing is not executed.
2. Subsequent processing of reprogramming processing is executed.
3. When the lock bit protection is disabled by the user program, the operation 'subsequent processing executed' cannot be selected with the ROM. Always choose the operation 'subsequent processing not executed' with the ROM.

Table 5.2 No. 1: Settings in r_flash_api_rx_config.h

Changed Contents	Code after the Change
The ROM is reprogrammed (program executed in the RAM).	#define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING
Programming data is not stored in the RAM.	// #define FLASH_API_RX_CFG_FLASH_TO_FLASH
Wait for completion of reprogramming processing for the E2 DataFlash and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_DATA_FLASH_BGO
Wait for completion of reprogramming processing for the ROM and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_ROM_BGO
The lock bit protection is disabled automatically by the API.	#define FLASH_API_RX_CFG_IGNORE_LOCK_BITS

Table 5.3 No. 2: Settings in r_flash_api_rx_config.h

Changed Contents	Code after the Change
The ROM is reprogrammed (program executed in the RAM).	#define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING
Programming data is stored in the RAM.	#define FLASH_API_RX_CFG_FLASH_TO_FLASH
Subsequent processing is executed during reprogramming the E2 DataFlash.	#define FLASH_API_RX_CFG_DATA_FLASH_BGO
Subsequent processing is executed during reprogramming the ROM.	#define FLASH_API_RX_CFG_ROM_BGO
The lock bit protection is disabled automatically by the API.	#define FLASH_API_RX_CFG_IGNORE_LOCK_BITS

Table 5.4 No. 3: Settings in r_flash_api_rx_config.h

Changed Contents	Code after the Change
The ROM is reprogrammed (program executed in the RAM).	#define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING
Programming data is not stored in the RAM.	// #define FLASH_API_RX_CFG_FLASH_TO_FLASH
Wait for completion of reprogramming processing for the E2 DataFlash and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_DATA_FLASH_BGO
Wait for completion of reprogramming processing for the ROM and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_ROM_BGO
The lock bit protection is disabled by the user program.	// #define FLASH_API_RX_CFG_IGNORE_LOCK_BITS

Table 5.5 No. 4: Settings in r_flash_api_rx_config.h

Changed Contents	Code after the Change
The ROM is reprogrammed (program executed in the RAM).	#define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING
Programming data is stored in the RAM.	#define FLASH_API_RX_CFG_FLASH_TO_FLASH
Subsequent processing is executed during reprogramming the E2 DataFlash.	#define FLASH_API_RX_CFG_DATA_FLASH_BGO
Wait for completion of reprogramming processing for the ROM and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_ROM_BGO
The lock bit protection is disabled by the user program.	// #define FLASH_API_RX_CFG_IGNORE_LOCK_BITS

Table 5.6 No. 5: Settings in r_flash_api_rx_config.h

Changed Contents	Code after the Change
The ROM is reprogrammed (program executed in the RAM).	#define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING
Programming data is not stored in the RAM.	// #define FLASH_API_RX_CFG_FLASH_TO_FLASH
Wait for completion of reprogramming processing for the E2 DataFlash and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_DATA_FLASH_BGO
Wait for completion of reprogramming processing for the ROM and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_ROM_BGO
The lock bit program is disabled automatically by the API.	#define FLASH_API_RX_CFG_IGNORE_LOCK_BITS

Table 5.7 No. 6: Settings in r_flash_api_rx_config.h

Changed Contents	Code after the Change
The ROM is reprogrammed (program executed in the RAM).	#define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING
Programming data is stored in the RAM.	#define FLASH_API_RX_CFG_FLASH_TO_FLASH
Wait for completion of reprogramming processing for the E2 DataFlash and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_DATA_FLASH_BGO
Subsequent processing is executed during reprogramming the ROM.	#define FLASH_API_RX_CFG_ROM_BGO
The lock bit program is disabled automatically by the API.	#define FLASH_API_RX_CFG_IGNORE_LOCK_BITS

Table 5.8 No. 7: Settings in r_flash_api_rx_config.h

Changed Contents	Code after the Change
The ROM is reprogrammed (program executed in the RAM).	#define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING
Programming data is not stored in the RAM.	// #define FLASH_API_RX_CFG_FLASH_TO_FLASH
Wait for completion of reprogramming processing for the E2 DataFlash and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_DATA_FLASH_BGO
Wait for completion of reprogramming processing for the ROM and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_ROM_BGO
The lock bit protection is disabled by the user program.	// #define FLASH_API_RX_CFG_IGNORE_LOCK_BITS

Table 5.9 No. 8: Settings in r_flash_api_rx_config.h

Changed Contents	Code after the Change
The ROM is reprogrammed (program executed in the RAM).	#define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING
Programming data is not stored in the RAM.	// #define FLASH_API_RX_CFG_FLASH_TO_FLASH
Wait for completion of reprogramming processing for the E2 DataFlash and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_DATA_FLASH_BGO
Wait for completion of reprogramming processing for the ROM and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_ROM_BGO
The lock bit program is disabled automatically by the API (default).	#define FLASH_API_RX_CFG_IGNORE_LOCK_BITS

Table 5.10 No. 9: Settings in r_flash_api_rx_config.h

Changed Contents	Code after the Change
The ROM is reprogrammed (program executed in the RAM).	#define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING
Programming data is stored in the RAM.	#define FLASH_API_RX_CFG_FLASH_TO_FLASH
Subsequent processing is executed during reprogramming the E2 DataFlash.	#define FLASH_API_RX_CFG_DATA_FLASH_BGO
Wait for completion of reprogramming processing for the ROM and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_ROM_BGO
The lock bit program is disabled automatically by the API (default).	#define FLASH_API_RX_CFG_IGNORE_LOCK_BITS

Table 5.11 No. 10: Settings in r_flash_api_rx_config.h

Changed Contents	Code after the Change
The ROM is not reprogrammed.	// define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING
Programming data is not stored in the RAM.	// #define FLASH_API_RX_CFG_FLASH_TO_FLASH
Wait for completion of reprogramming processing for the E2 DataFlash and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_DATA_FLASH_BGO
Wait for completion of reprogramming processing for the ROM and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_ROM_BGO
The lock bit program is disabled automatically by the API (default).	#define FLASH_API_RX_CFG_IGNORE_LOCK_BITS

Table 5.12 No. 11: Settings in r_flash_api_rx_config.h

Changed Contents	Code after the Change
The ROM is not reprogrammed.	// define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING
Programming data is stored in the RAM.	#define FLASH_API_RX_CFG_FLASH_TO_FLASH
Subsequent processing is executed during reprogramming the E2 DataFlash.	#define FLASH_API_RX_CFG_DATA_FLASH_BGO
Wait for completion of reprogramming processing for the ROM and the subsequent processing is not executed.	// #define FLASH_API_RX_CFG_ROM_BGO
The lock bit program is disabled automatically by the API (default).	#define FLASH_API_RX_CFG_IGNORE_LOCK_BITS

5.2 Selecting an Operation During Reprogramming

When the operation 'subsequent processing executed' is selected as an operation during reprogramming, the flash ready interrupt generation is enabled and completion of reprogramming is confirmed in the interrupt handling.

The interrupt priority level of the flash ready interrupt is shown in Table 5.13.

If the flash ready interrupt and another interrupt occur simultaneously, a higher priority interrupt is executed first.

Table 5.13 Interrupt Priority Level of the Flash Ready Interrupt

Setting	Code after the Level is Set
The priority level of the flash ready interrupt is set to 5.	<code>#define FLASH_API_RX_CFG_FLASH_READY_IPL 5</code>

The following four functions must be written in the reprogramming program. Use the functions adding required processing.

Refer to the section "Using Non-Blocking Background Operations" in the Simple Flash API for RX application note.

- void FlashEraseDone(void)
- void FlashWriteDone(void)
- void FlashBlankCheckDone(uint8_t result)
- void FlashError(void)

When the operation 'subsequent processing executed' is selected, make sure that registers which are write disabled must not be rewritten within the loop of the processing during ROM/E2 DataFlash P/E mode. When in ROM/E2 DataFlash P/E mode, processing in the loop including additional processing are executed in P/E mode.

5.3 Method of Transferring the Reprogramming API to the RAM

When APIs used for reprogramming are executed in the RAM, the APIs need to be transferred from the ROM to the RAM. The transfer method can be selected from the following two methods.

- Transfer is performed at a given timing.
- Transfer is performed immediately after a reset.

Table 5.14 and Table 5.15 list definitions in `r_flash_api_rx_config.h` for each method.

Table 5.14 Settings in `r_flash_api_rx_config.h` (Transfer at a Given Timing)

Setting	Code after Setting
The ROM is reprogrammed (program executed in the RAM).	<code>#define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING</code>
The <code>R_FlashCodeCopy</code> function is used to transfer programs.	<code>#define FLASH_API_RX_CFG_COPY_CODE_BY_API</code>

Table 5.15 Settings in `r_flash_api_rx_config.h` (Transfer Immediately After a Reset)

Setting	Code after Setting
The ROM is reprogrammed (program executed in the RAM).	<code>#define FLASH_API_RX_CFG_ENABLE_ROM_PROGRAMMING</code>
The <code>R_FlashCodeCopy</code> function is not used to transfer programs.	<code>// #define FLASH_API_RX_CFG_COPY_CODE_BY_API</code>

Note: • When selecting the method to transfer immediately after a reset, the `dbstc.c` file which is made when generating the project needs to be modified.

When the reprogramming program is executed in the RAM, write codes for transferring the program from the ROM to the RAM after a reset.

- When using the `R_FlashCodeCopy` function for ROM to RAM transfer, add processing to call the `R_FlashCodeCopy` function.
- When not using the `R_FlashCodeCopy` function for ROM to RAM transfer, add a code to the `dbstc.c` file as shown in red below.

```
{ __sectop("D"), __secend("D"), __sectop("R") },
{ __sectop("D_2"), __secend("D_2"), __sectop("R_2") },
{ __sectop("D_1"), __secend("D_1"), __sectop("R_1") },
{ __sectop("PFRAM"), __secend("PFRAM"), __sectop("RPFRAM") }
```

6. Additional Setting in the Integrated Development Environment

The following settings are required to specify sections in the integrated development environment.

For details on the settings, refer to the section "Putting Flash API Code in RAM" in the Simple Flash API for RX application note.

- Define the PFRAM section in the ROM area.
- Define the RPFRAM section in the RAM area.
- Specify the linker setting so that code in the FRAM section is executed in the RAM.

7. Software

7.1 Operation Overview

This section describes the sample code for the reprogramming program.

The ROM and the E2 DataFlash are reprogrammed using APIs from the Simple Flash API.

In the reprogramming areas, all areas in the E2 DataFlash and blocks 255 to 16 in the ROM are erased, and the content in the start address of each block is reprogrammed to the following:

"hello world0123456789abcdefghijklmnopqrstuvwxyzABCDEFGHIJKLMNOPQRSTUVWXYZ".

Figure 7.1 shows the Memory Map.

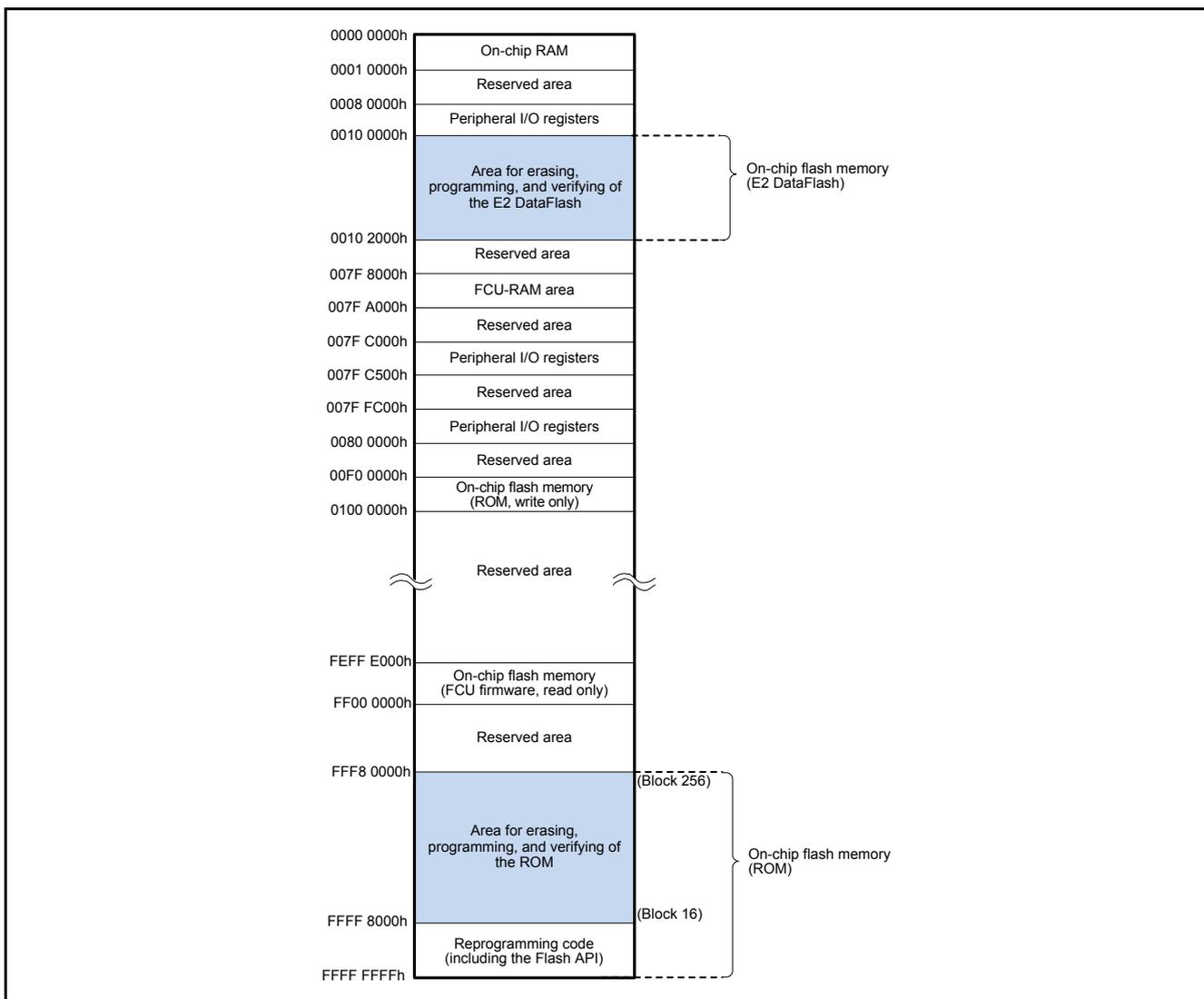


Figure 7.1 Memory Map

7.2 File Composition

Table 7.1 lists the Files Used in the Sample Code, Table 7.2 lists the Standard Include File, Table 7.3 lists the Functions and Their Settings in the RX210 Group Initial Setting Application Note, and Table 7.4 lists the File in the Simple Flash API. Files generated by the integrated development environment are not included in this table.

Table 7.1 Files Used in the Sample Code

File Name	Outline	Remarks
main.c	Main processing	
flash_write_main.c	Sample processing for reprogramming the ROM and the E2 DataFlash	
flash_api_rx.c	Flash memory reprogramming program (Simple Flash API)	r_flash_api_rx.c modified as described in 4.4
flash_api_rx_if.h	Header file for flash_api_rx.c	r_flash_api_rx_if.h modified as described in 4.2
flash_api_rx210.h	Header file for flash_api_rx.c	r_flash_api_rx210.h modified as described in 4.3

Table 7.2 Standard Include File

File Name	Outline
stdbool.h	Defines macros associated with Boolean and its value.
stdint.h	Defines macros declaring the integer type with the specified width.
machine.h	Defines types of intrinsic functions for the RX Family.

Table 7.3 Functions and Their Settings in the RX210 Group Initial Setting Application Note

File Name	Function	Contents
r_init_stop_module.c	R_INIT_StopModule()	—
r_init_stop_module.h	—	Module-stop state is canceled for DMAC/DTC, EXDMAC, RAM0, and RAM1.
r_init_non_existent_port.c	R_INIT_NonExistentPort()	—
r_init_non_existent_port.h	—	100-pin package is specified.
r_init_clock.c	R_INIT_Clock()	—
r_init_clock.h	—	Clock setting No. 1 is specified.

Table 7.4 File in the Simple Flash API

(RX600 & RX200 Series Simple Flash API for RX application note)

File Name	Function	Contents
r_flash_api_rx_config.h	—	<ul style="list-style-type: none"> - Reprograms the ROM and the E2 DataFlash. - Executes reprogramming processing in the RAM, waits for the completion of the reprogramming. The subsequent processing is not executed. - Lock bit protection is disabled by the API.

7.3 Option-Setting Memory

Table 7.5 lists the Option-Setting Memory Configured in the Sample Code. When necessary, set a value suited to the user system.

Table 7.5 Option-Setting Memory Configured in the Sample Code

Symbol	Address	Setting Value	Contents
OFS0	FFFF FF8Fh to FFFF FF8Ch	FFFF FFFFh	The IWDT is stopped after a reset. The WDT is stopped after a reset.
OFS1	FFFF FF8Bh to FFFF FF88h	FFFF FFFFh	The voltage monitor 0 reset is disabled after a reset. HOCO oscillation is disabled after a reset.
MDES	FFFF FF83h to FFFF FF80h	FFFF FFFFh	Little endian
MDEB	FF7F FFF8h to FF7F FFFBh	FFFF FFFFh	Little endian

7.4 Constants

Table 7.6 lists the Constants Used in the Sample Code.

Table 7.6 Constants Used in the Sample Code

Constant Name	Setting Value	Contents
E2FLASH_WRITE_START	0	Reprogramming of the E2 DataFlash started
E2FLASH_WRITE_ERASE	1	Erasing the E2 DataFlash
E2FLASH_WRITE_BLANK	2	Blank checking the E2 DataFlash
E2FLASH_WRITE_PROGRAM	3	Programming the E2 DataFlash
E2FLASH_WRITE_FIN	4	E2 DataFlash reprogramming completed
FLASH_WRITE_START	0	Reprogramming of the ROM started
FLASH_WRITE_ERASE	1	Erasing the ROM
FLASH_WRITE_PROGRAM	2	Programming the ROM
FLASH_WRITE_FIN	3	ROM reprogramming completed
ROM_RESERVED_BYTES	32768	Storage size for the reprogramming program
E2FLASH_WRITE_ENABLE	Enabled	Reprogramming of the E2 DataFlash enabled
FLASH_WRITE_ENABLE	Enabled	Reprogramming of the ROM enabled

7.5 Variables

Table 7.7 lists the Global Variables.

Table 7.7 Global Variables

Type	Variable Name	Contents	Function Used
uint8_t	E2Flash_WriteStatus	Status of E2 DataFlash reprogramming	main
uint8_t	Flash_WriteStatus	Status of ROM reprogramming	main

7.6 Functions

Table 7.8 lists the Functions.

Table 7.8 Functions

Function Name	Outline
main	Main processing
flash_write	Reprogramming flash memory
E2Flash_Write_start	Reprogramming E2 DataFlash (subsequent processing is executed during programming)
E2Flash_Write	Reprogramming E2 DataFlash
Flash_Write_start	Reprogramming ROM (subsequent processing is executed during programming)
Flash_Write	Reprogramming ROM
rom_bgo_init	Transferring relocatable vector to RAM
lock_bit_tests	Disabling ROM lock bit protection

7.7 Function Specifications

The following tables list the sample code function specifications.

main	
Outline	Main processing
Header	None
Declaration	void main(void);
Description	After initialization, the function for reprogramming the flash memory is called.
Arguments	None
Return Value	None
flash_api	
Outline	Reprogramming flash memory
Header	None
Declaration	void flash_api (void)
Description	The function for reprogramming the flash memory is executed. The function to be executed is selected according to the enable/disable setting of reprogramming and the selected operation during reprogramming.
Arguments	None
Return Value	None
E2Flash_Write_start	
Outline	Reprogramming E2 DataFlash (subsequent processing is executed during programming)
Header	None
Declaration	static void E2Flash_Write_start (void)
Description	Reprogramming of the E2 DataFlash is executed. If the FCU command is issued successfully, the subsequent processing is executed until the command execution is completed.
Arguments	None
Return Value	None
E2Flash_Write	
Outline	Reprogramming E2 DataFlash
Header	None
Declaration	static void E2Flash_Write (void)
Description	Reprogramming of the E2 DataFlash is executed. If the FCU command is issued, a loop is performed within the processing until the command execution is completed.
Arguments	None
Return Value	None

Flash_Write_start	
Outline	Reprogramming ROM (subsequent processing is executed during programming)
Header	None
Declaration	static void Flash_Write_start (void)
Description	Reprogramming of the ROM is executed. If the FCU command is issued successfully, the subsequent processing is executed until the command execution is completed.
Arguments	None
Return Value	None

Flash_Write	
Outline	Reprogramming ROM
Header	None
Declaration	static void Flash_Write (void)
Description	Reprogramming of the ROM is executed. After issuing the FCU command, a loop is performed within the processing until the command execution is completed.
Arguments	None
Return Value	None

rom_bgo_init	
Outline	Transferring relocatable vector to RAM
Header	None
Declaration	static void rom_bgo_init(void)
Description	The relocatable vector table is transferred to the RAM to use the flash ready interrupt.
Arguments	None
Return Value	None

lock_bit_tests	
Outline	Disabling ROM lock bit protection
Header	None
Declaration	static void lock_bit_tests (void)
Description	Lock bit protection is disabled for the ROM. If the result of the issued read lock bit status command is "lock bit enabled", the lock bit protection is disabled and block erasing is executed.
Arguments	None
Return Value	None

7.8 Flowcharts

7.8.1 Main Processing

Figure 7.2 shows the Main Processing.

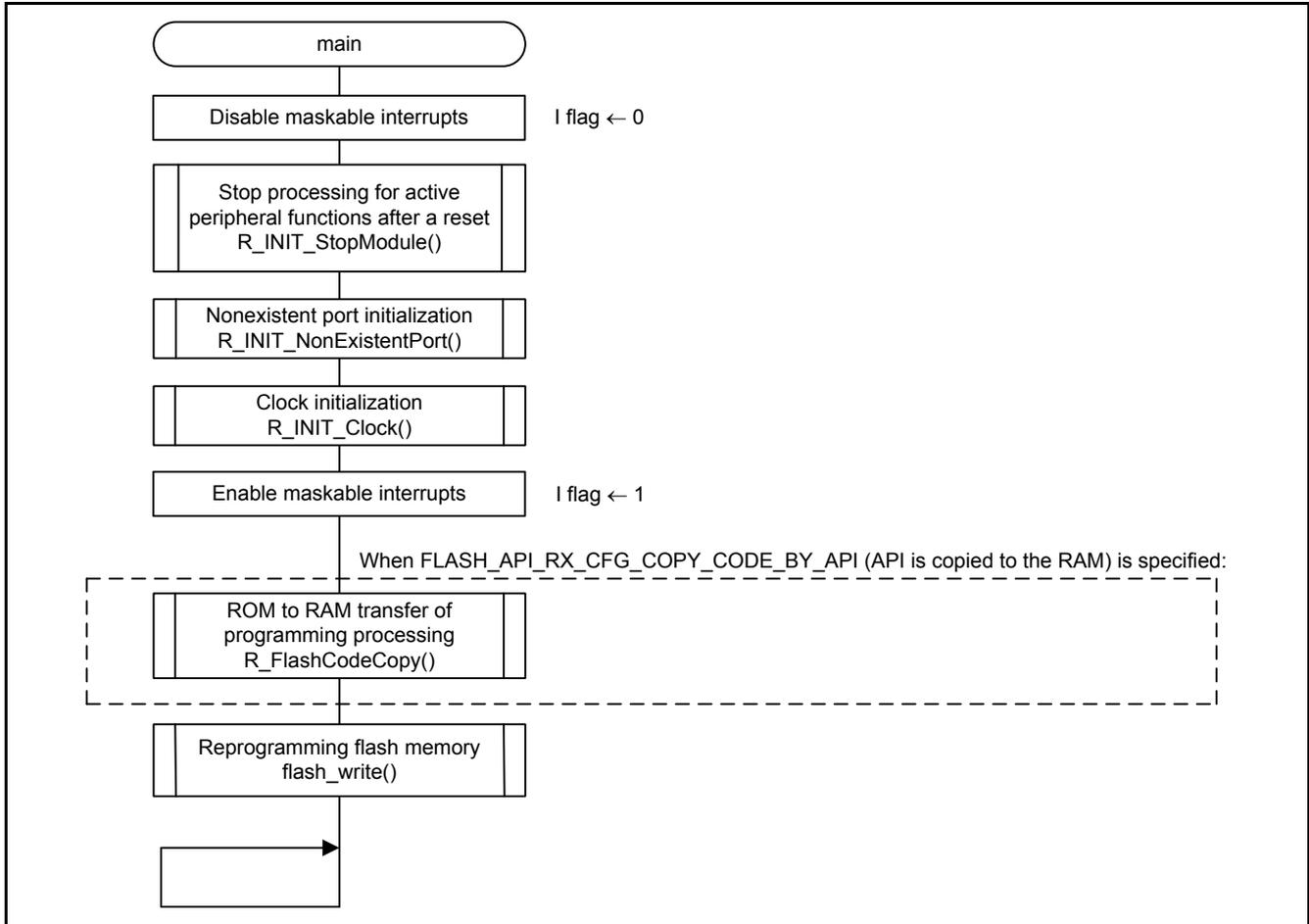


Figure 7.2 Main Processing

7.8.2 Reprogramming Flash Memory

Figure 7.3 shows the Reprogramming Flash Memory.

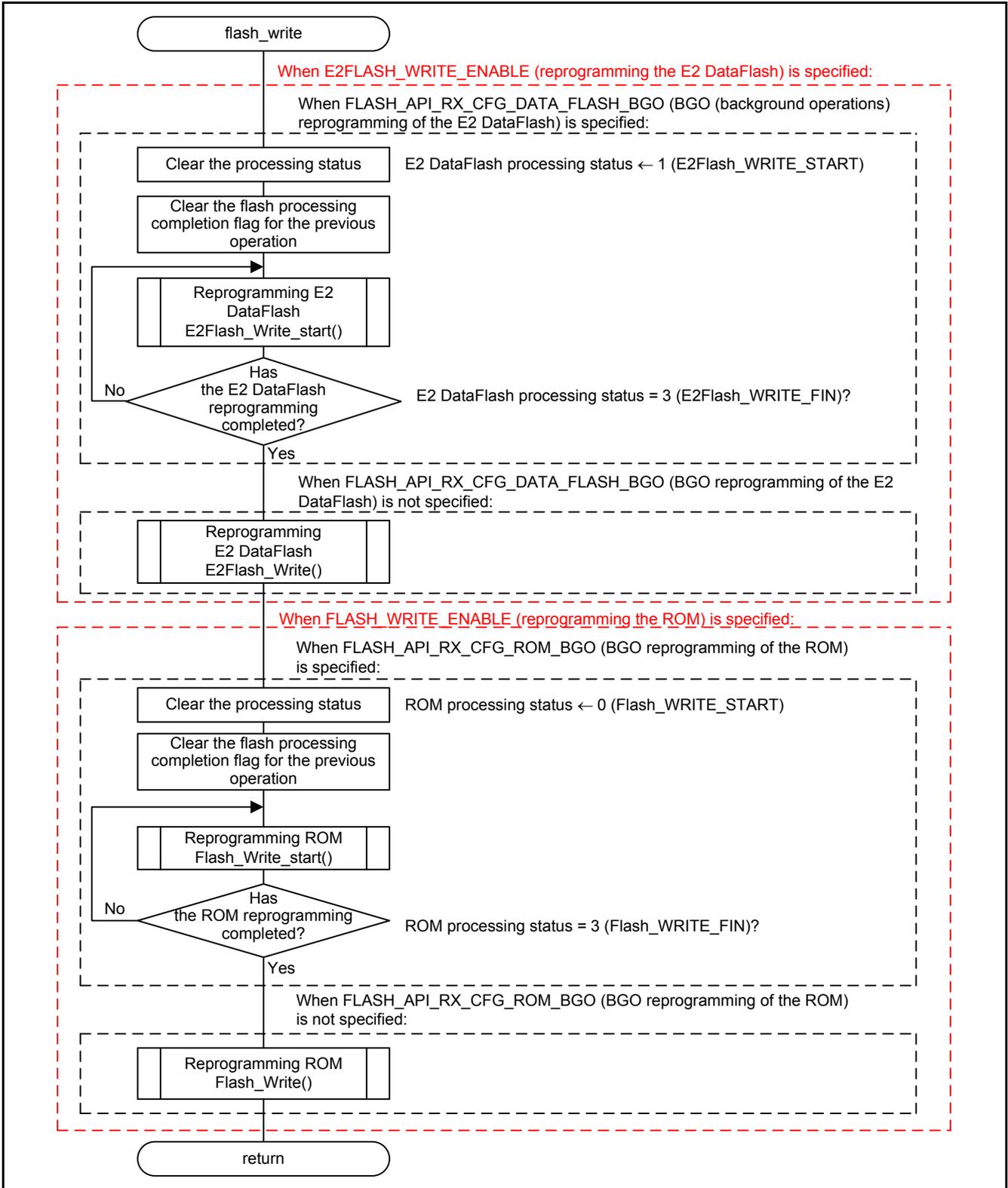


Figure 7.3 Reprogramming Flash Memory

**7.8.3 Reprogramming E2 DataFlash
(Subsequent Processing is Executed During Programming)**

Figure 7.4 and Figure 7.5 show the Reprogramming E2 DataFlash (Subsequent Processing is Executed During Programming).

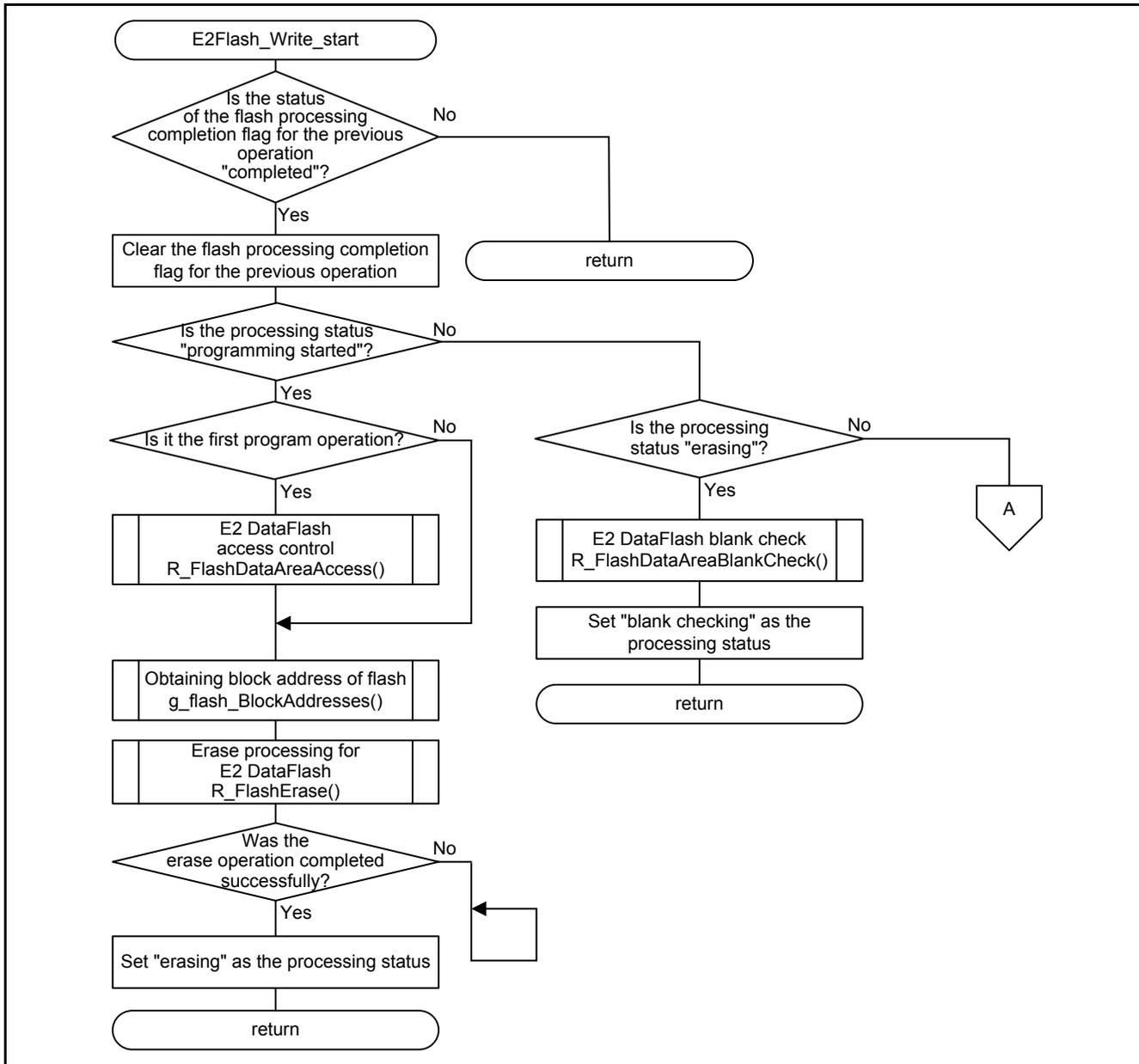


Figure 7.4 Reprogramming E2 DataFlash (Subsequent Processing is Executed During Programming) (1/2)

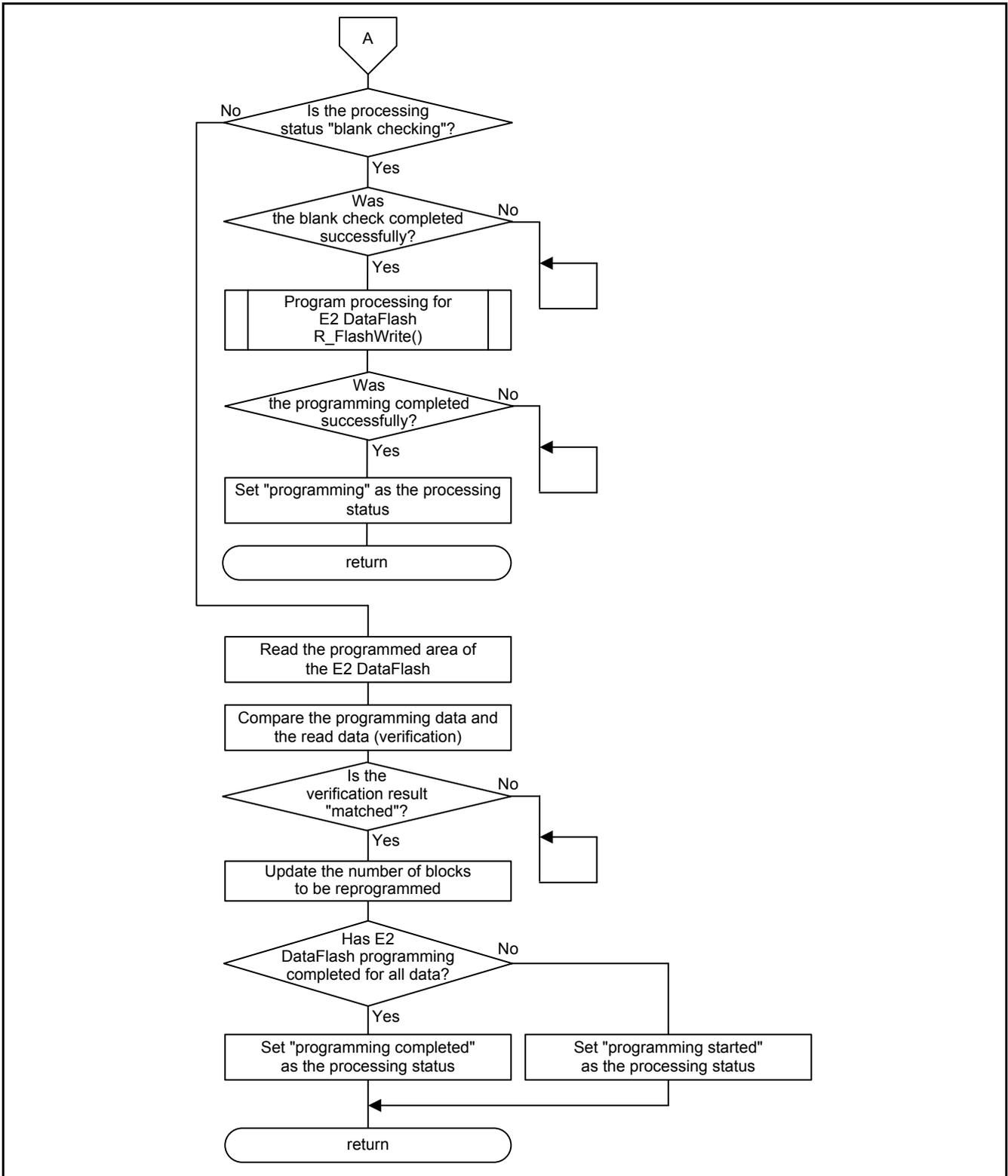


Figure 7.5 Reprogramming E2 DataFlash (Subsequent Processing is Executed During Programming) (2/2)

7.8.4 Reprogramming E2 DataFlash

Figure 7.6 shows the Reprogramming E2 DataFlash.

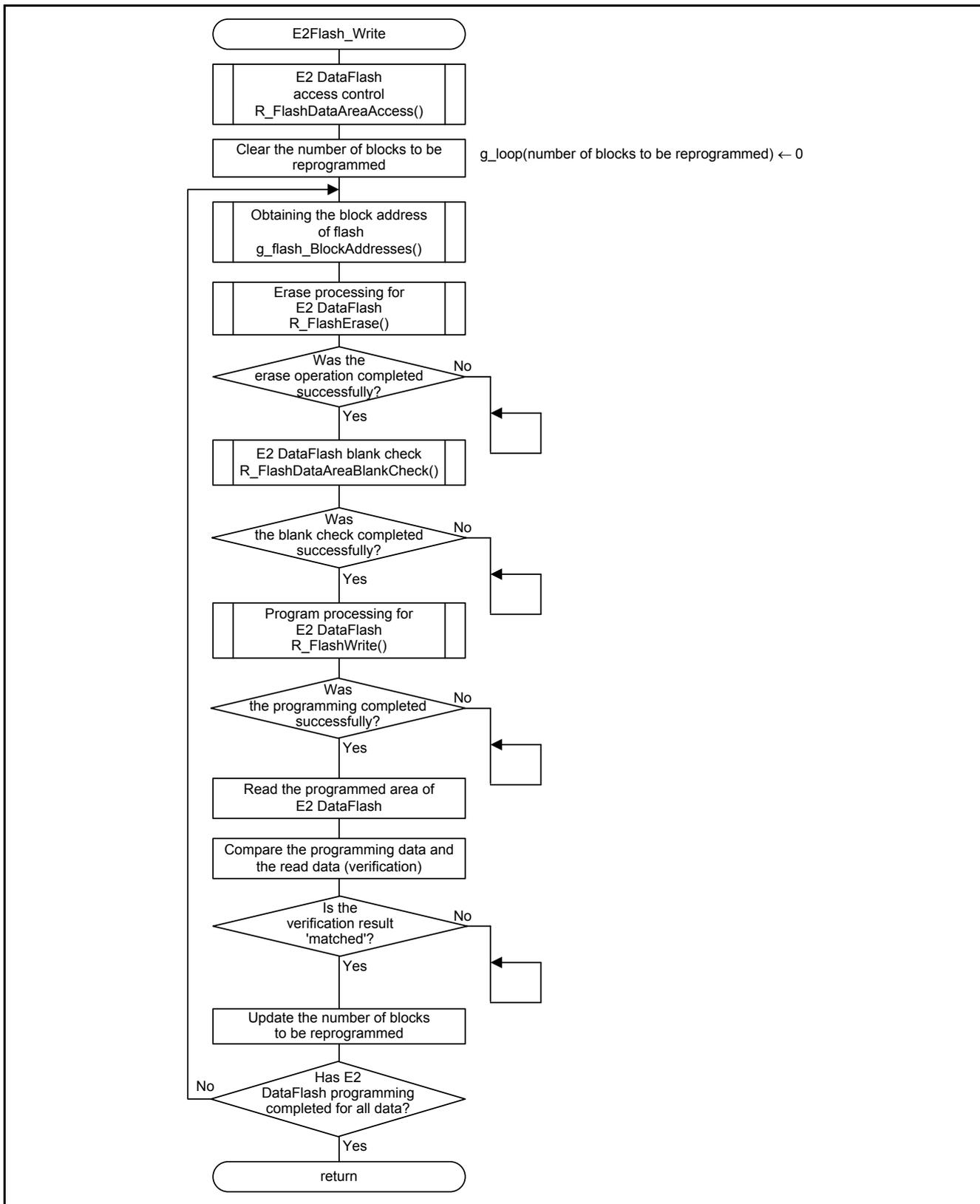


Figure 7.6 Reprogramming E2 DataFlash

7.8.5 Reprogramming ROM (Subsequent Processing is Executed During Programming)

Figure 7.7 and Figure 7.8 show the Reprogramming ROM (Subsequent Processing is Executed During Programming).

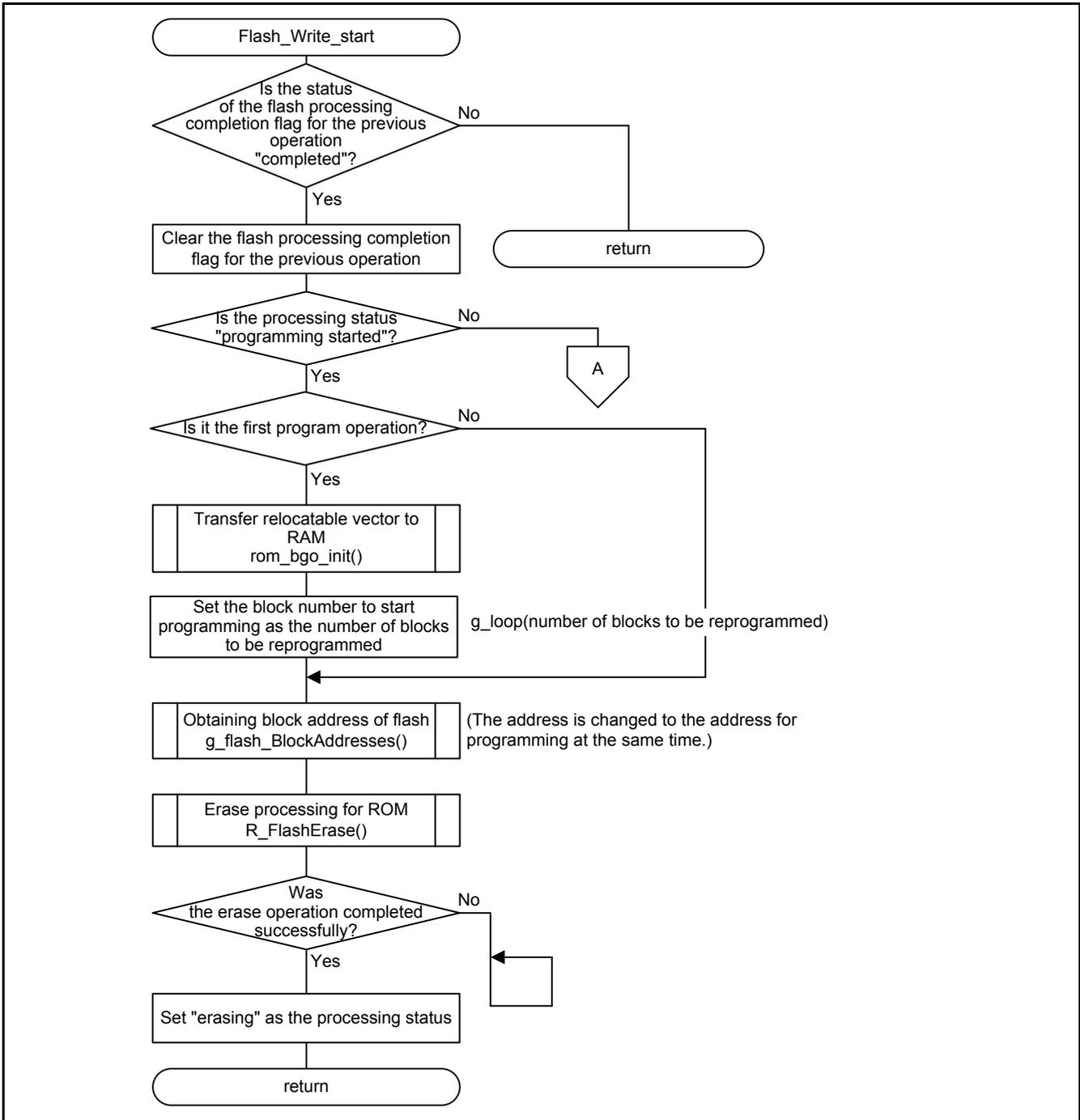


Figure 7.7 Reprogramming ROM (Subsequent Processing is Executed During Programming) (1/2)

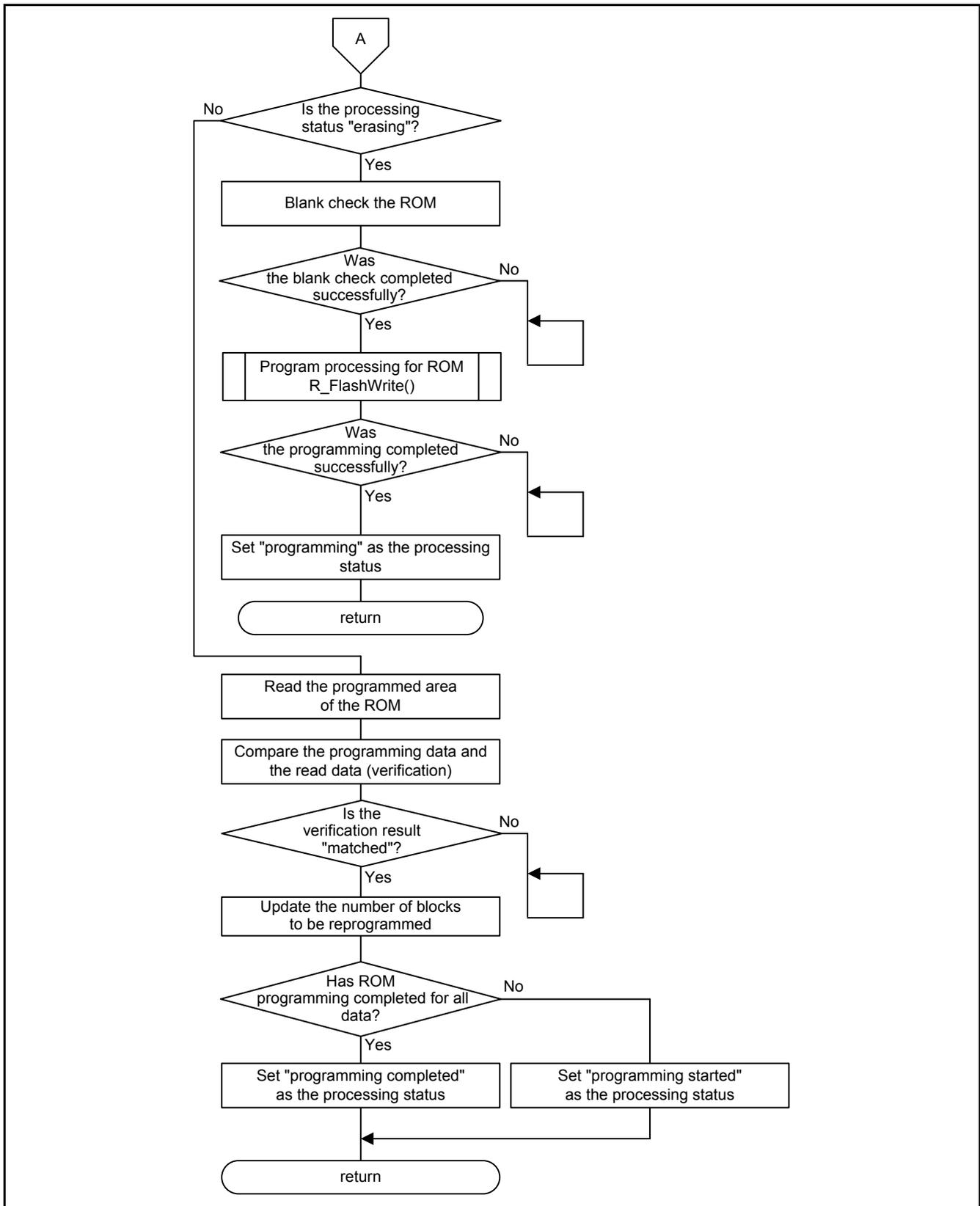


Figure 7.8 Reprogramming ROM
(Subsequent Processing is Executed During Programming) (2/2)

7.8.6 Reprogramming ROM

Figure 7.9 shows the Reprogramming ROM.

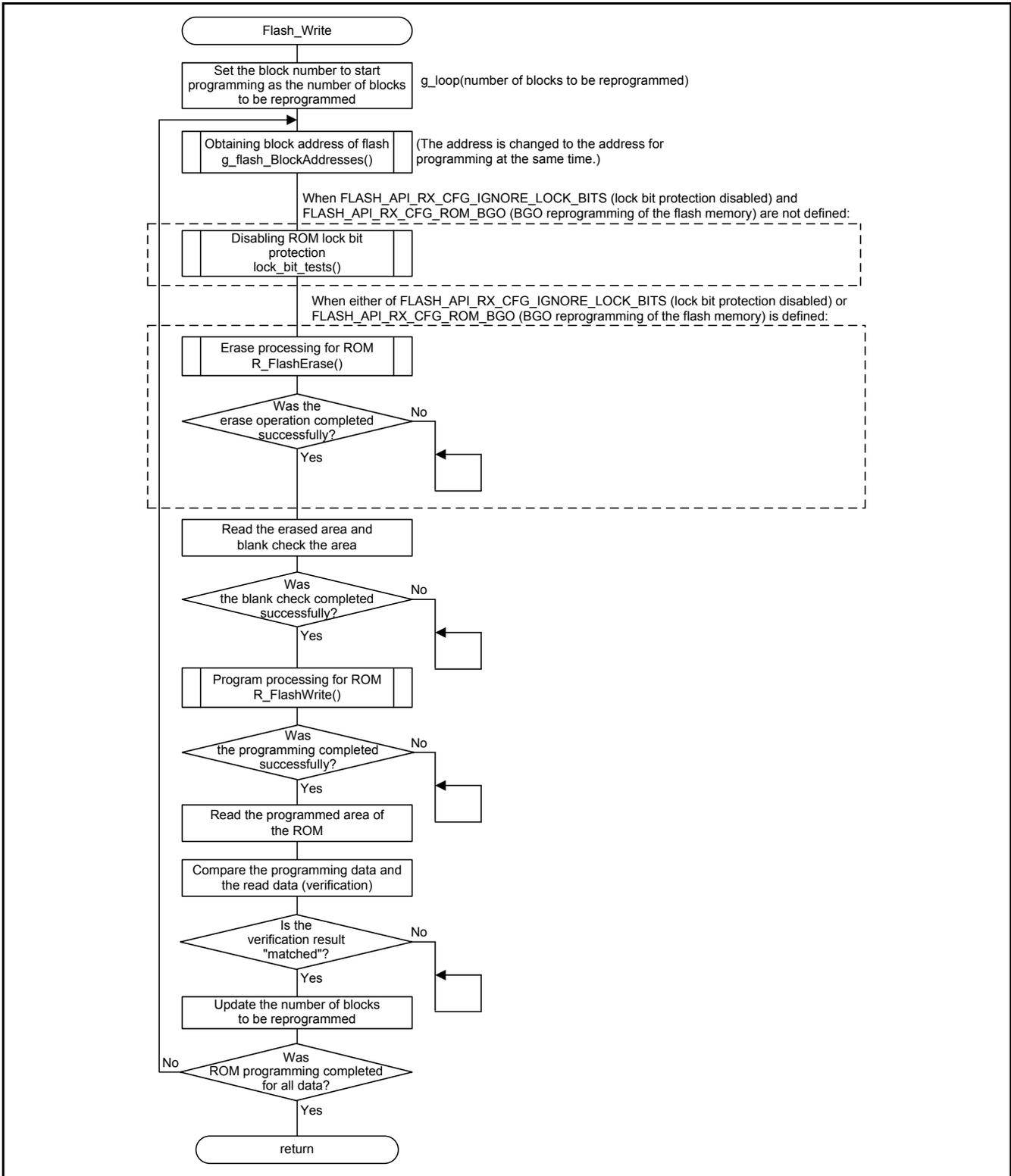


Figure 7.9 Reprogramming ROM

7.8.7 Transferring Relocatable Vector to RAM

Figure 7.10 shows the Transferring Relocatable Vector to RAM.

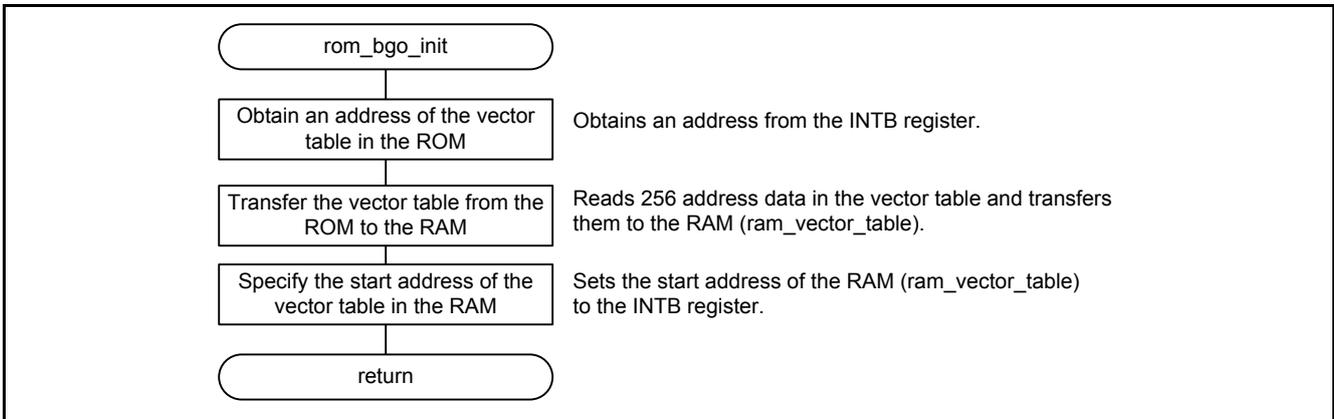


Figure 7.10 Transferring Relocatable Vector to RAM

7.8.8 Disabling ROM Lock Bit Protection

Figure 7.11 shows the Disabling ROM Lock Bit Protection.

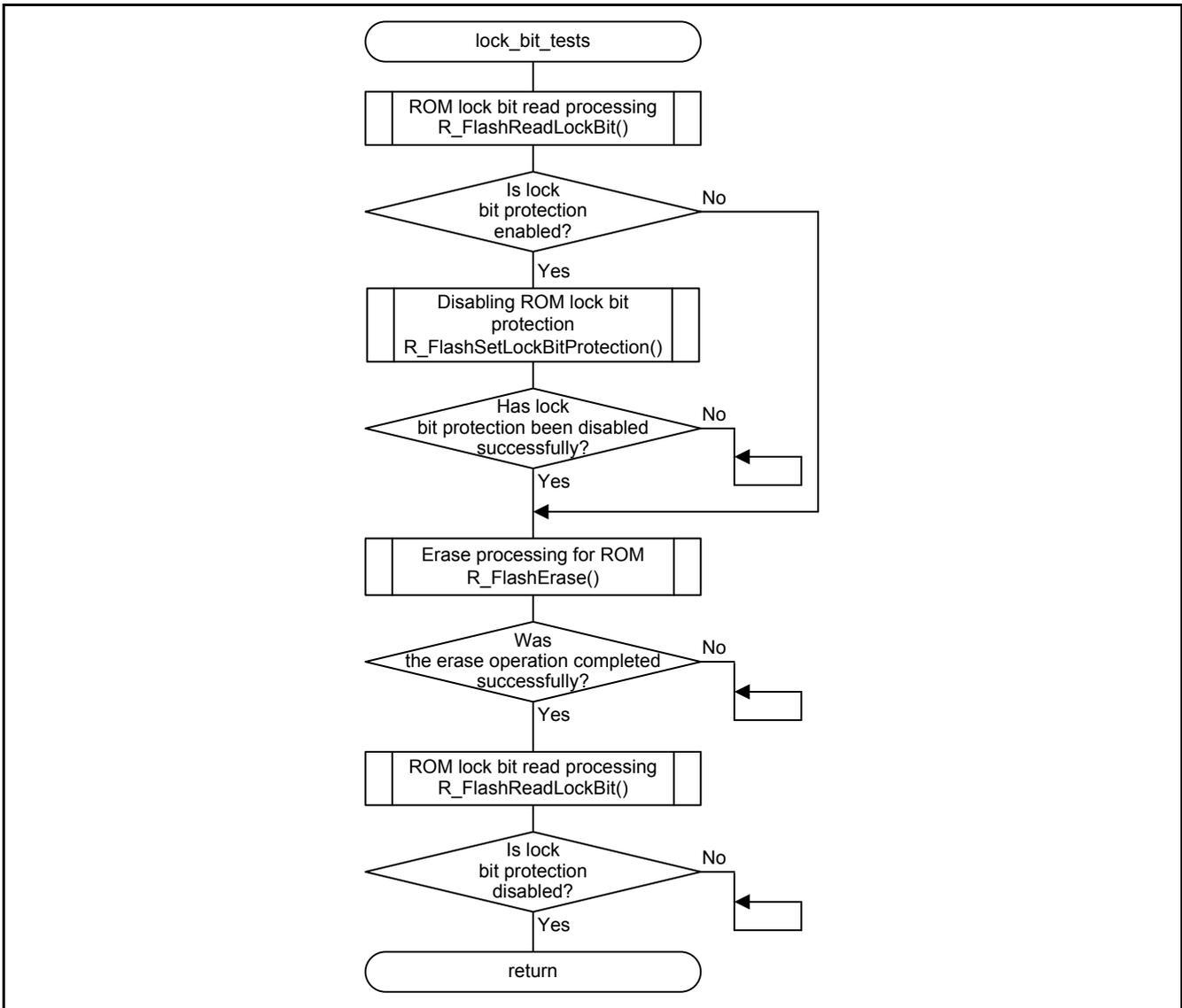


Figure 7.11 Disabling ROM Lock Bit Protection

8. Sample Code

Sample code can be downloaded from the Renesas Electronics website.

9. Reference Documents

User's Manual: Hardware

RX210 Group User's Manual: Hardware Rev.1.50 (R01UH0037EJ)

The latest version can be downloaded from the Renesas Electronics website.

Technical Update/Technical News

The latest information can be downloaded from the Renesas Electronics website.

User's Manual: Development Tools

RX Family C/C++ Compiler Package V.1.01 User's Manual Rev.1.00 (R20UT0570EJ)

The latest version can be downloaded from the Renesas Electronics website.

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REVISION HISTORY	RX600 & RX200 Series Application Note Reprogramming the On-Chip Flash Memory Using Simple Flash API for RX
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Rev.	Date	Description	
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